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(54) **HETEROJUNCTION SEMICONDUCTOR FLEXIBLE SUBSTRATE, MANUFACTURING METHOD THEREOF, AND ELECTRONIC DEVICE USING THE SAME**

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(57) **ABSTRACT**  
Disclosed is a heterojunction semiconductor flexible substrate in which an epitaxial oxide thin film layer is hetero-bonded to a thinned silicon substrate using a metal layer, a manufacturing method thereof, and the heterojunction semiconductor flexible substrate can be applied to sensor, actuator, transducer, or micro electro mechanical systems (MEMS) device using high functionality of the epitaxial oxide thin film layer of high quality as well as an electronic and/or optical device.

